Amendments to the Claims

The current listing of the claims replaces all previous amendments and listings of the claims.

1. (Currently Amended) A ceramic heater comprising:

a ceramic substrate comprising a heating face configured to heat a wafer;

an insulating layer having a thickness of between 0.1 and 1000 μm and a volume resistivity higher than that of said ceramic substrate~~, being formed~~ and disposed on ~~at least a part of~~ a surface of said ceramic substrate; and

a resistance heating element ~~formed~~ disposed on an opposite side of the heating face and disposed on said insulating layer.

2. (Original) The ceramic heater according to claim 1,

wherein said ceramic substrate comprises a carbide ceramic or a nitride ceramic and said insulating layer comprises an oxide ceramic.

3. and 4. (Canceled)

5. (Currently Amended) The ceramic heater according to claim 1,

wherein the volume resistivity of said insulating layer is ~~not less than~~ at least 10 times ~~larger than~~ the volume resistivity of said ceramic substrate.

6. (Currently Amended) A ceramic heater comprising;

a ceramic substrate comprising a heating face, the ceramic substrate warped in one direction;

a supporting pin disposed in the heating face; and

a resistance heating element ~~formed~~ disposed on a surface of said ceramic substrate~~,~~ ~~wherein said ceramic substrate is warped in one direction~~ and disposed on an opposite side of the heating face.

7.-30. (Canceled)

31. (New) The ceramic heater according to claim 1,

wherein the insulating layer has a thickness between 1 and 1000 μm.

32. (New) The ceramic heater according to claim 1,

wherein a supporting pin is disposed in the heating face.

33. (New) The ceramic heater according to claim 1, further comprising:

means for holding a silicon wafer between 50 and 2000 μm from the heating face and for heating the silicon wafer.

34. (New) The ceramic heater according to claim 1,

wherein the ceramic substrate comprises a carbide ceramic or a nitride ceramic.

35. (New) The ceramic heater according to claim 32,

wherein the supporting pin comprises a tip having a spired form or a semicircular form.

36. (New) The ceramic heater according to claim 6,

wherein the ceramic substrate is warped between 20 and 100 μm.

37. (New) The ceramic heater according to claim 6,

wherein the ceramic substrate is warped greater 25 μm and less than or equal to 100 μm.

38. (New) The ceramic heater according to claim 6, further comprising:

means for holding a silicon wafer between 50 and 2000 μm from the heating face and for heating the silicon wafer.